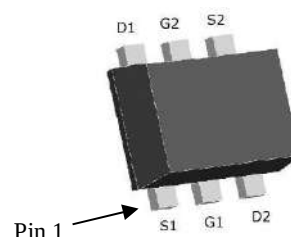


Dual N-Channel Enhancement Mode MOSFET

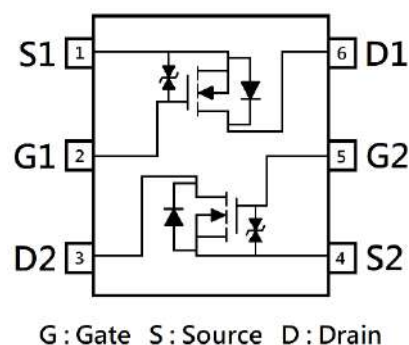
Features:

- ESD protected gate, typical 2kV (HBM)
- High speed switching
- Easily designed drive circuits
- Low-voltage drive
- Easy to use in parallel
- RoHS compliant package

SOT-563



BV_{DSS}	60V
$I_D @ V_{GS}=4.5V, T_A=25^\circ C$	0.29A
$R_{DS(ON) typ.} @ V_{GS}=4.5V, I_D=0.2A$	1.3 Ω
$R_{DS(ON) typ.} @ V_{GS}=2.5V, I_D=0.1A$	1.7 Ω



Ordering Information

Device	Package	Shipping
KWAK6-56	SOT-563 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (T_A=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ V _{GS} =4.5V, T _A =25°C	I _D	0.29	A
Continuous Drain Current @ V _{GS} =4.5V, T _A =70°C		0.23	
Pulsed Drain Current *a	I _{DM}	1.2	
Continuous Body Diode Forward Current @ T _A =25°C	I _S	0.29	
ESD susceptibility *b	V _{ESD}	2000	V
Total Power Dissipation @ T _A =25°C	P _D	0.42	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	R _{θJA}	245	°C/W

Note:

*a. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

*b. Human body model, 1.5kΩ in series with 100pF.

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	60	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	0.5	-	1.5		V _{DS} =V _{GS} , I _D =250μA
G _{FS}	-	0.5	-	S	V _{DS} =5V, I _D =0.2A
I _{GSS}	-	-	±10	μA	V _{GS} =±16V, V _{DS} =0V
I _{DSS}	-	-	1		V _{DS} =48V, V _{GS} =0V
R _{DS(ON)}	-	1.3	3	Ω	V _{GS} =4.5V, I _D =0.2A
	-	1.7	5		V _{GS} =2.5V, I _D =0.1A
Dynamic					
C _{iss}	-	25	-	pF	V _{DS} =30V, V _{GS} =0V, f=1MHz
C _{oss}	-	8	-		
C _{rss}	-	7	-		
Q _g *1, 2	-	0.75	-	nC	V _{DS} =30V, I _D =0.2A, V _{GS} =4.5V
Q _{gs} *1, 2	-	0.35	-		
Q _{gd} *1, 2	-	0.15	-		
t _{d(ON)} *1, 2	-	3	-	ns	V _{DS} =30V, I _D =0.2A, V _{GS} =4.5V, R _{GS} =25Ω
t _r *1, 2	-	16	-		
t _{d(OFF)} *1, 2	-	11	-		
t _f *1, 2	-	16	-		
Source-Drain Diode					
V _{SD} *1	-	0.8	1.2	V	I _S =0.2A, V _{GS} =0V
t _{rr}	-	9	-	ns	I _F =0.2A, dI _F /dt=100A/μs
Q _{rr}	-	2.7	-	nC	

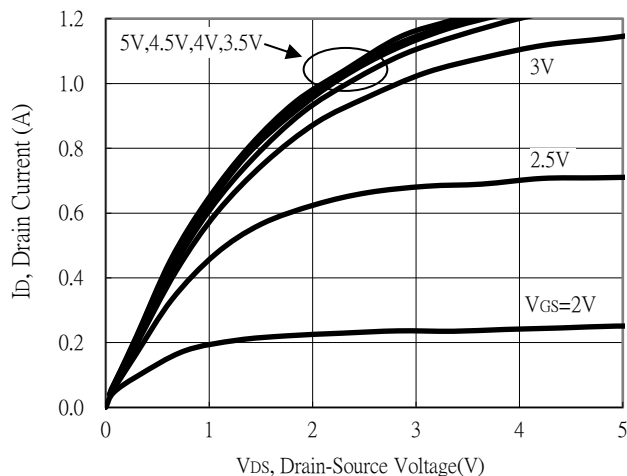
Note:

*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

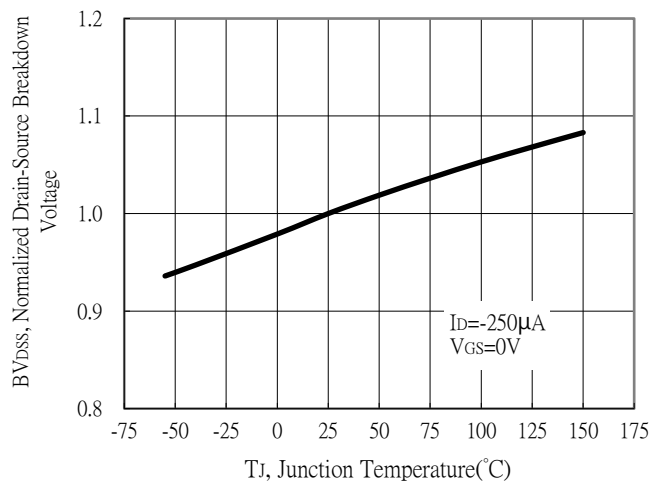
*2. Independent of operating temperature

Typical Characteristics

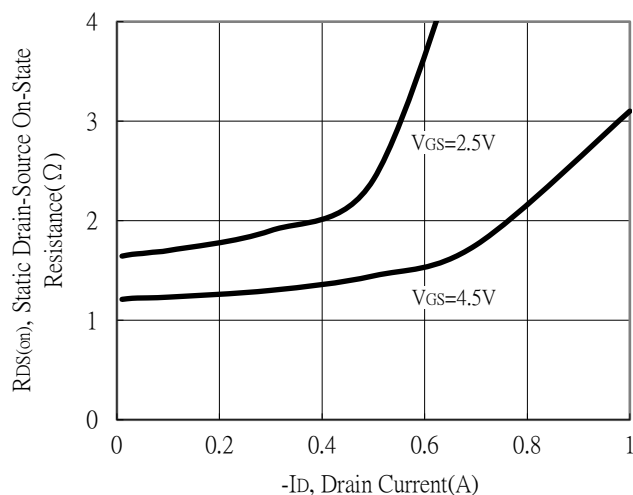
Typical Output Characteristics



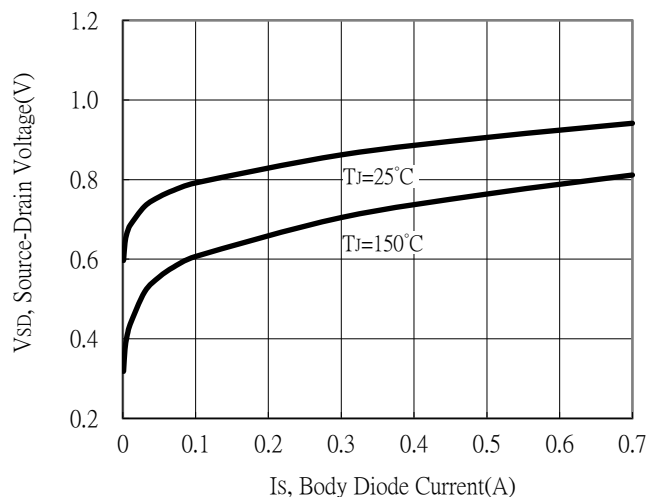
Breakdown Voltage vs Junction Temperature



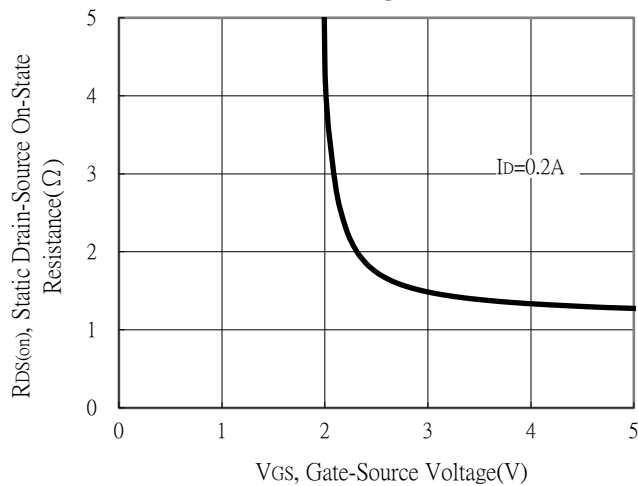
Static Drain-Source On-State resistance vs Drain Current



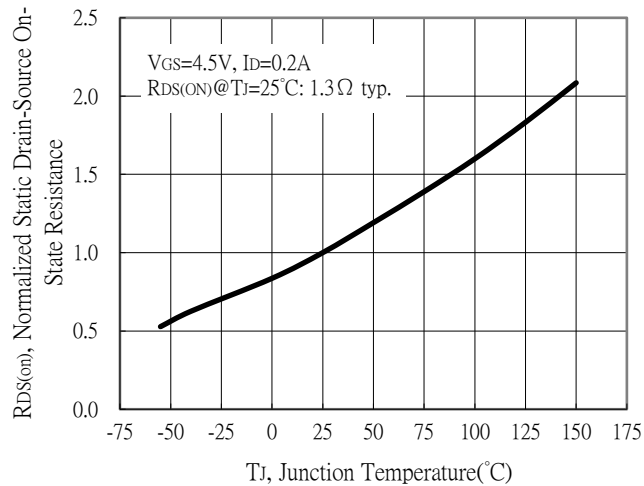
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

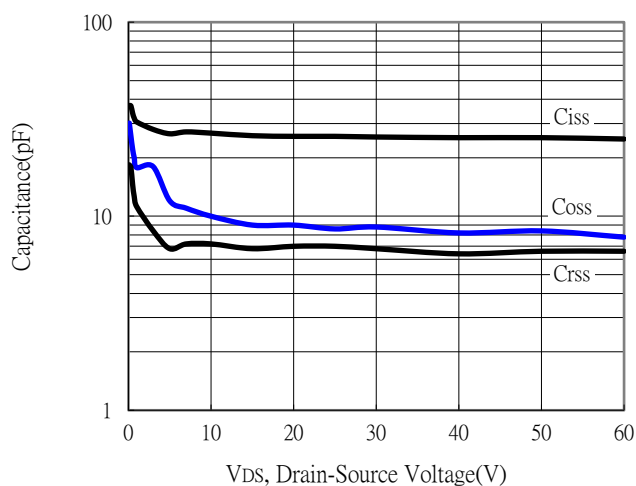


Drain-Source On-State Resistance vs Junction Temperature

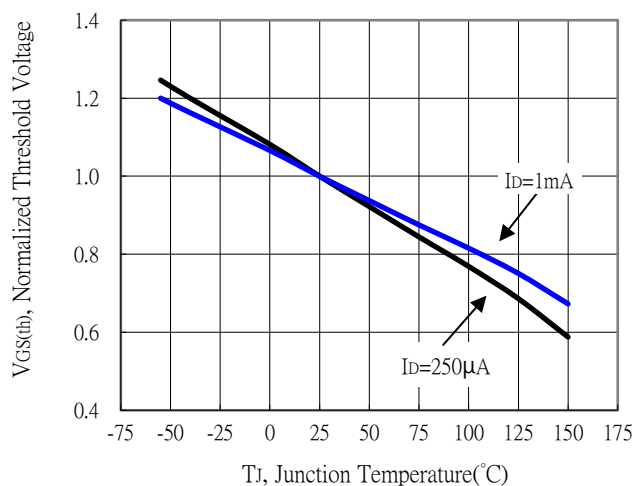


Typical Characteristics (Cont.)

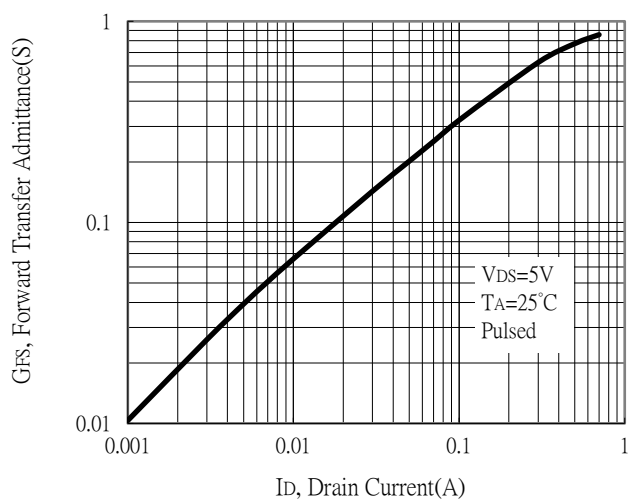
Capacitance vs Drain-to-Source Voltage



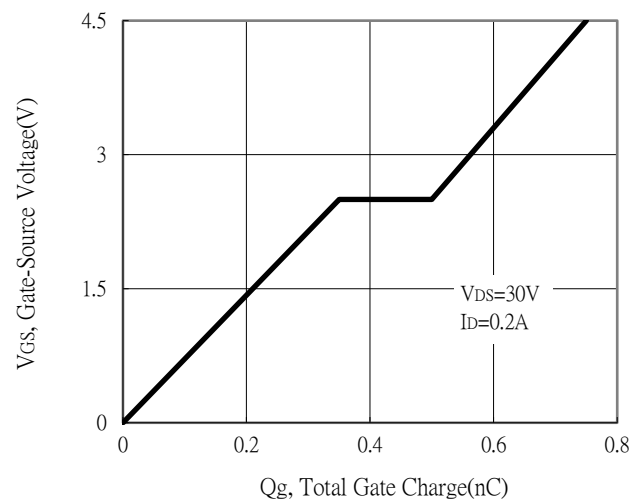
Threshold Voltage vs Junction Temperature



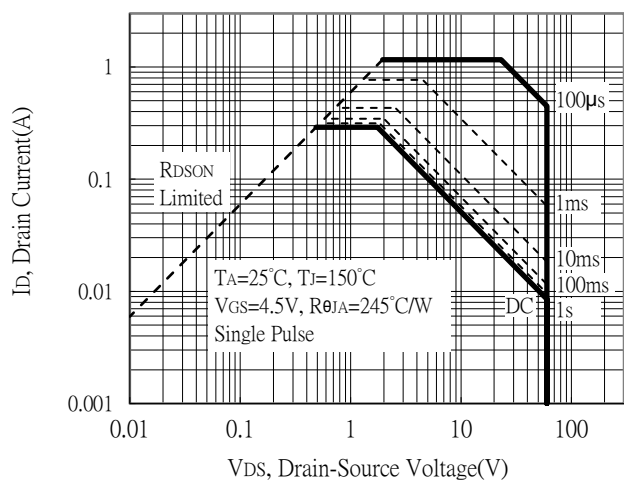
Forward Transfer Admittance vs Drain Current



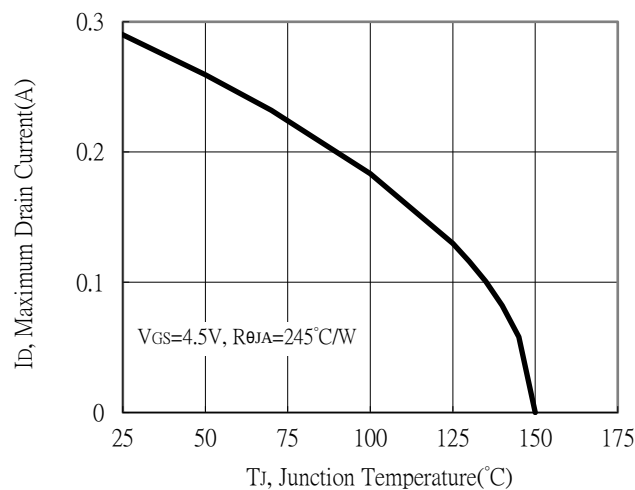
Gate Charge Characteristics



Maximum Safe Operating Area

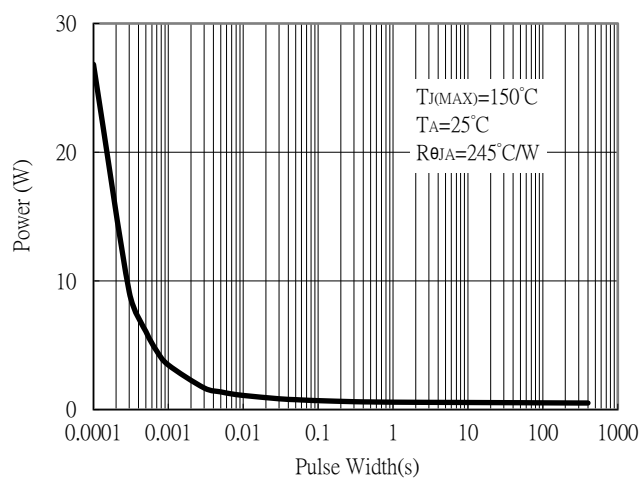


Maximum Drain Current vs Junction Temperature

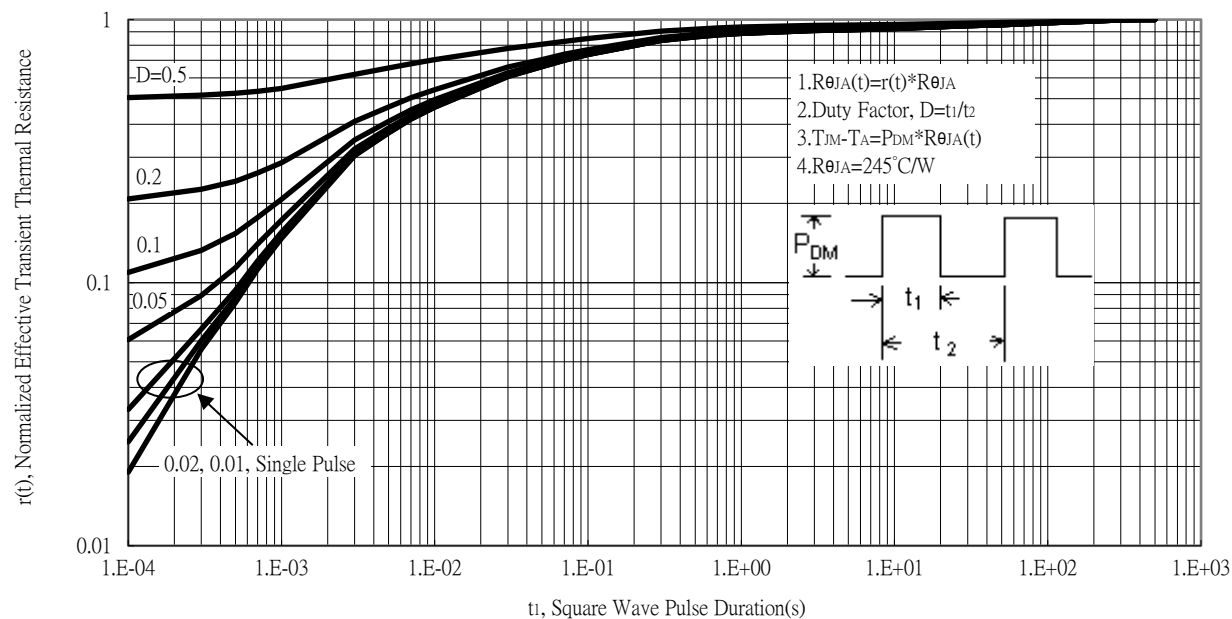


Typical Characteristics (Cont.)

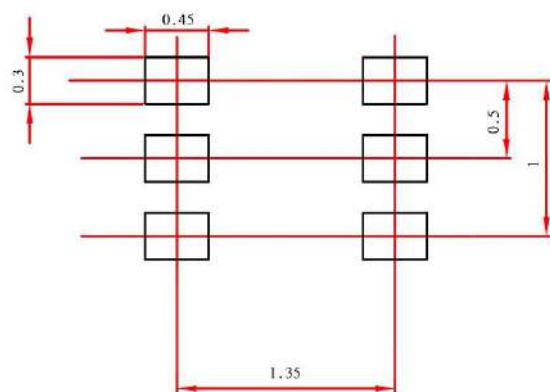
Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves

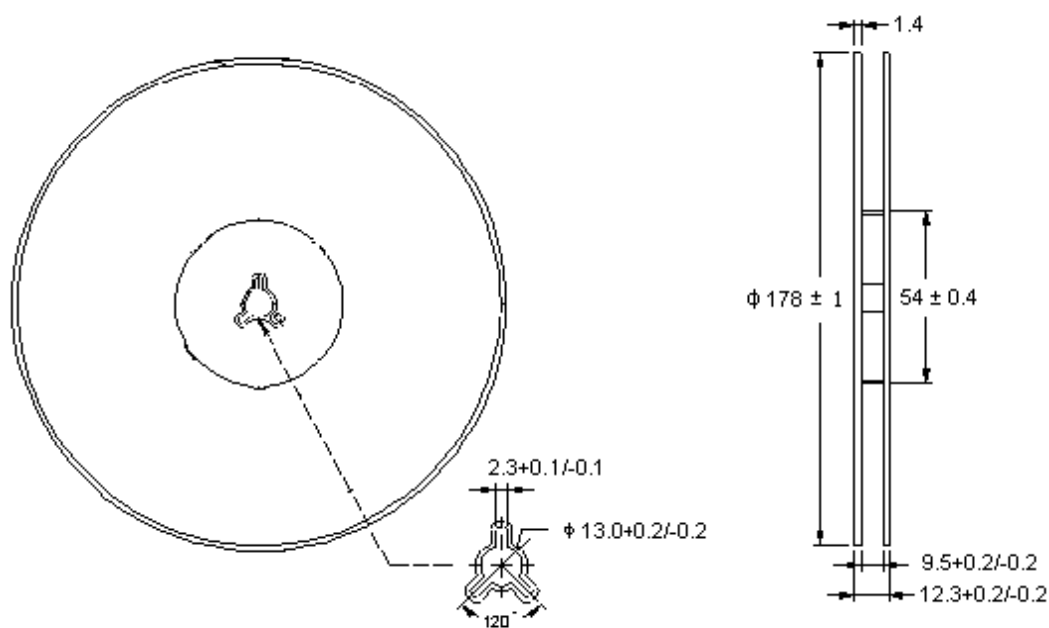


Recommended Soldering Footprint



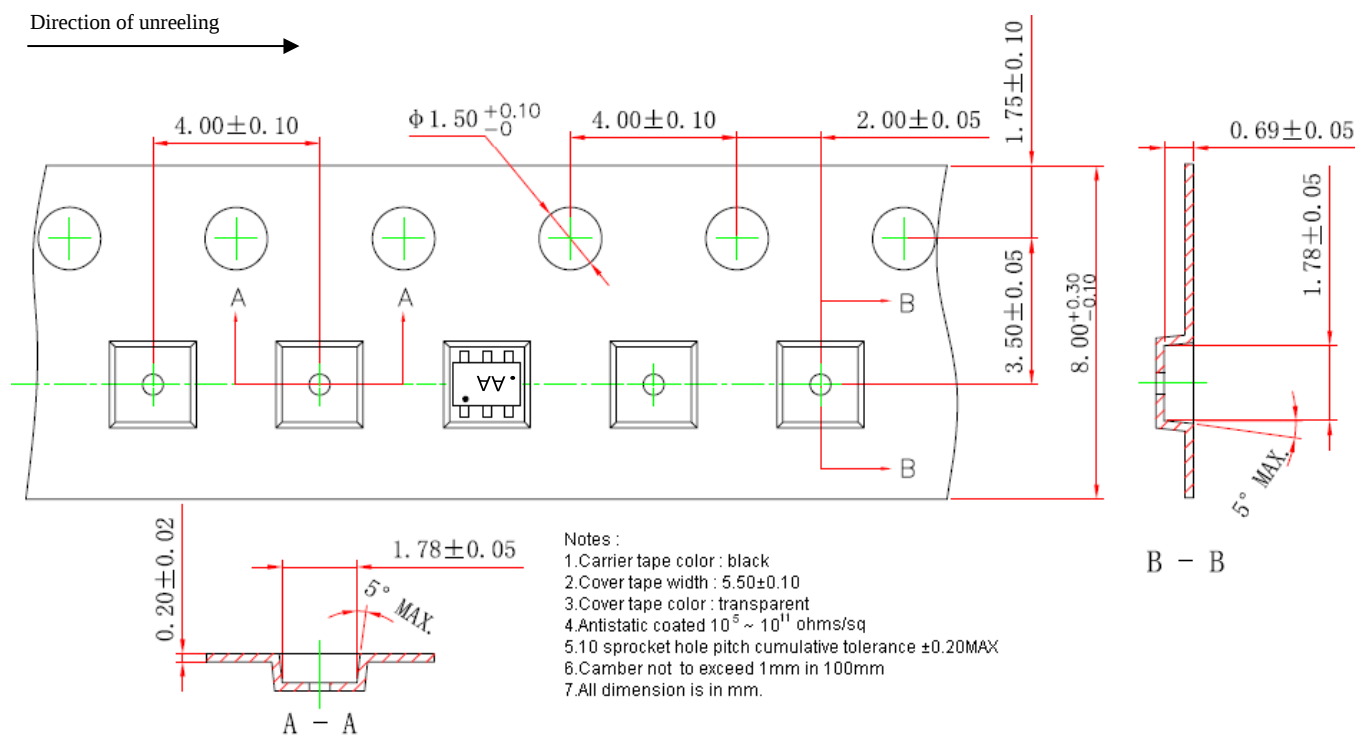
unit:mm

Reel Dimension

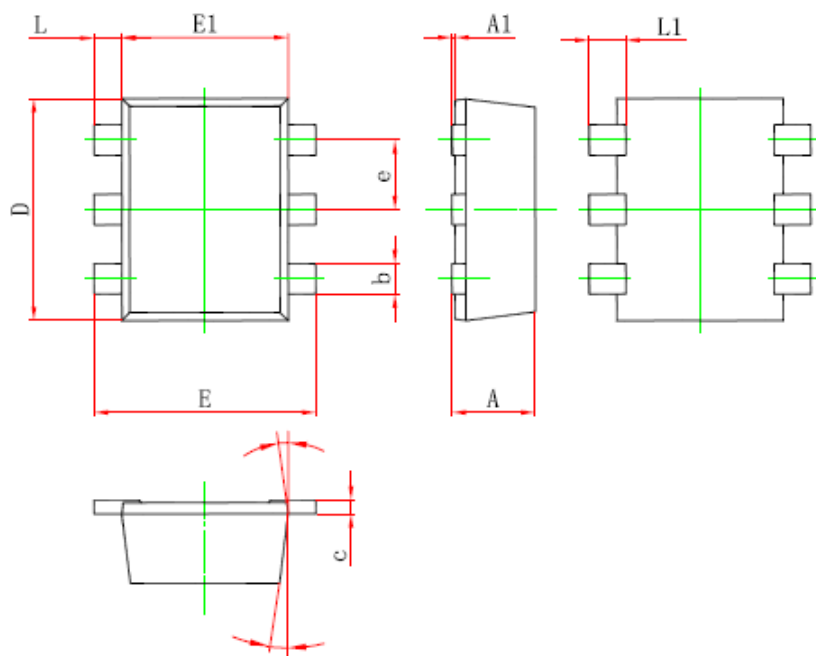


Unit: millimeter

Carrier Tape Dimension

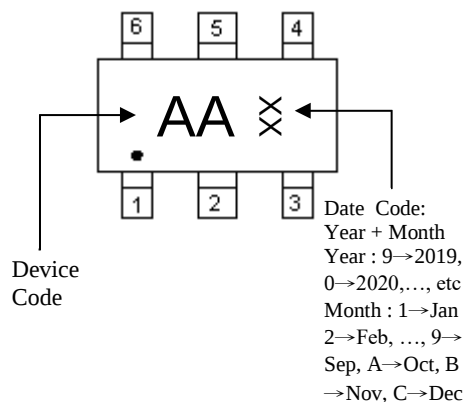


SOT-563 Dimension



6-Lead SOT-563 Plastic
Surface Mounted Package

Marking:



Style:

- Pin 1. Source1 (S1)
- Pin 2. Gate1 (G1)
- Pin 3. Drain2 (D2)
- Pin 4. Source2 (S2)
- Pin 5. Gate2 (G2)
- Pin 6. Drain1 (D1)

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.021	0.024	0.525	0.600	E1	0.043	0.051	1.100	1.300
A1	0.000	0.002	0.000	0.050	E	0.059	0.067	1.500	1.700
e	0.018	0.022	0.450	0.550	L	0.004	0.012	0.100	0.300
c	0.004	0.006	0.090	0.160	L1	0.008	0.016	0.200	0.400
D	0.059	0.067	1.500	1.700	θ	7° REF		7° REF	
b	0.007	0.011	0.170	0.270					